

PATENT ABSTRACTS OF JAPAN

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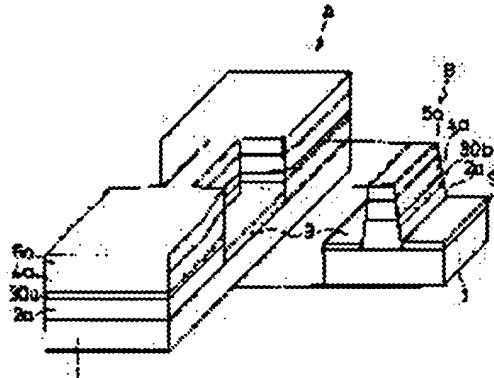
(21)Application number : 04-359673 (71)Applicant : MITSUBISHI ELECTRIC CORP
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(54) SEMICONDUCTOR OPTICAL DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

PURPOSE: To obtain a semiconductor laser having an active layer, in which the laser outgoing end-face side is thinned and the inside of a laser is formed in thick layer thickness, on a flat surface having no stepped section and manufacture thereof.

CONSTITUTION: Two striped SiO₂ films 9 are formed in parallel while mutually forming a regular interval in a region positioned in a laser resonator shaped onto a GaAs substrate 1 on the GaAs substrate 1, and AlGaAs clad layers 2a are formed through an organometallic vapor growth method in an atomic-layer epitaxial mode. AlGaAs active layers 30a and 30b (the inside of a laser) are shaped through the organometallic vapor growth method in a normal mode, and AlGaAs clad layers 4a and GaAs clad layers 5a are formed through the organometallic vapor growth method in the atomic-layer epitaxial mode.



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